

isc Silicon NPN Power Transistor

DESCRIPTION

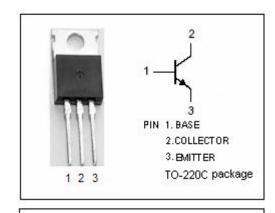
- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO}= 50V(Min)
- · Low Collector-Emitter Saturation Voltage-
 - : V_{CE(sat)}= 1.0V(Max) @I_C= 2.0A
- · Complement to Type 2SB514
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

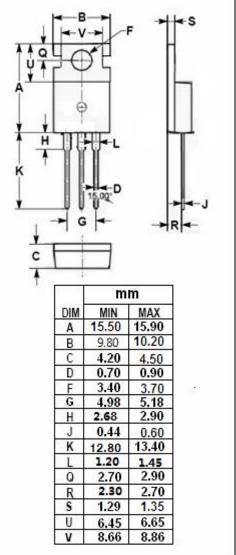


 Especially suited for use in output stage of 10W AF power amplifier.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{СВО}	Collector-Base Voltage	50	V	
V _{CEO}	Collector-Emitter Voltage	50	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	2	Α	
I _{CM}	Collector Current-Peak	5	Α	
Pc	Collector Power Dissipation @ T _a =25℃	1.75	W	
	Collector Power Dissipation @ T _C =25 ℃	20		
TJ	Junction Temperature	150	${\mathbb C}$	
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}\mathbb{C}$	







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2SD330

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA ; I _B = 0	50			V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 0.2A			1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 1A; V _{CE} = 5V			1.5	V
Ісво	Collector Cutoff Current	V _{CB} = 20V; I _E = 0			100	μА
ІЕВО	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 2V	40		320	
h _{FE-2}	DC Current Gain	I _C = 0.1A; V _{CE} = 2V	35			
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 5V		8		MHz

♦ h_{FE-1} Classifications

С	D	E	F
40-80	60-120	100-200	160-320

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